

**T-1 3/4 (5mm) INFRA-RED EMITTING
DIODE**

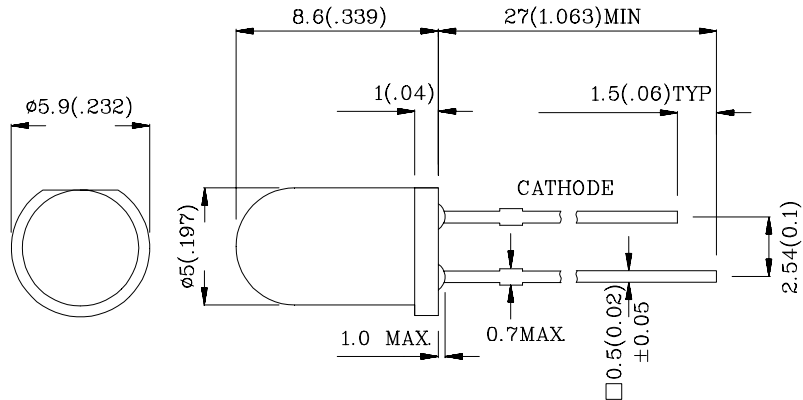


SUN LED

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XTNI53BF



Notes:

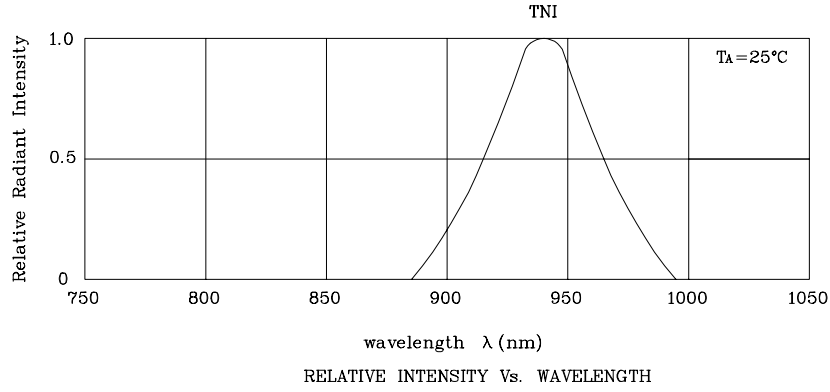
1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ " unless otherwise noted.

Absolute maximum ratings ($T_A=25^\circ\text{C}$)		TNI (GaAs)	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	50	mA
Forward current (peak) 1/100Duty cycle 10us pulse width	i_{FS}	1.2	A
Power dissipation	P_T	100	mW
Operating temperature	T_A	-40 ~ +85	°C
Storage temperature	T_{stg}	-40 ~ +85	
Lead solder temperature [2mm below package base]	260°C For 5 Seconds		

Operating Characteristics ($T_A=25^\circ\text{C}$)		TNI (GaAs)	Unit
Forward voltage (typ.) ($I_F=20\text{mA}$)	V_F	1.2	V
Forward voltage (max.) ($I_F=20\text{mA}$)	V_F	1.6	V
Reverse current ($V_R=5\text{V}$)	I_R	10	uA
Wavelength at peak emission ($I_F=20\text{mA}$)	λ_{peak}	940	nm
Spectral Line half-width ($I_F=20\text{mA}$)	$\Delta\lambda$	50	nm
Capacitance ($V_F=0\text{V}$, $f=1\text{MHz}$)	C	90	pF

Part Number	Emitting Material	Lens-color	Luminous Intensity ($I_F=20\text{mA}$ *50mA) mW/sr		Wavelength nm λ_P	Viewing Angle $2\theta_{1/2}$
			min.	typ.		
XTNI53BF	GaAs	Blue Transparent	5	19	940	30°
			*8	*27		

XTNI53BF



❖ TNI

